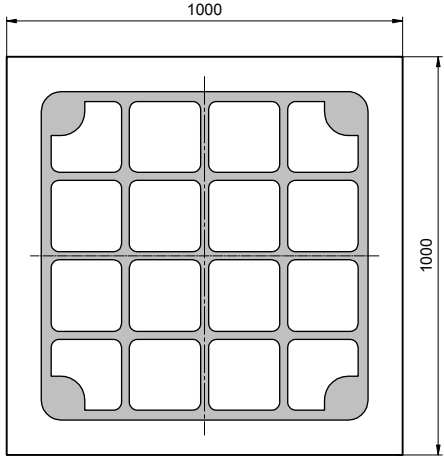


Radiation	Type	Technology	Electrodes
Infrared	DH	AlGaAs/GaAs	P (anode) up

	typ. dimensions (µm)	
	<u>typ. thickness</u> 270 (±25) µm <u>cathode</u> gold alloy, 0.5 µm structured, 25% covered <u>anode</u> gold alloy, 1.5 µm	

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F = 20 mA	V _F		1.1	1.3	V
Forward voltage ²	I _F = 350 mA	V _F		1.5	1.7	V
Reverse voltage	I _R = 10 µA	V _R	5			V
Radiant power ¹	I _F = 20 mA	Φ _e	1.0	1.3		mW
Radiant power ²	I _F = 350 mA	Φ _e	18	23		mW
Peak wavelength	I _F = 20 mA	λ _P	940	950	960	nm
Spectral bandwidth at 50%	I _F = 20 mA	Δλ _{0.5}		45		nm
Switching time	I _F = 20 mA	t _r , t _f		600		ns

¹Measured on bare chip on TO-18 header with *EPIGAP* equipment

²Measured on bare chip glued on a Ø 8 x 1mm Cu header (10 s after switched on) with *EPIGAP* equipment (for information only)

Labeling

Type	Lot N°	Φ _e (typ) [mW]	V _F (typ) [V]	Quantity
ELC-950-11				

Packing: Chips on adhesive film with wire-bond side on top